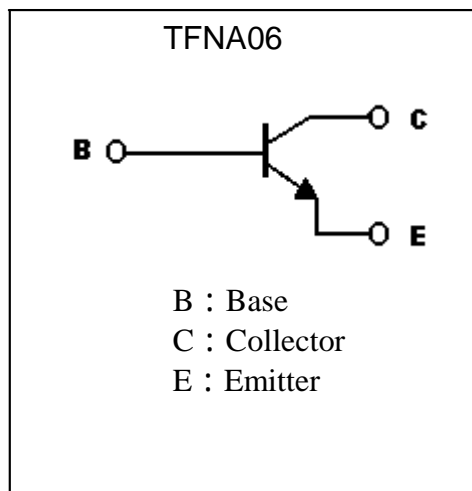


# TFNA06

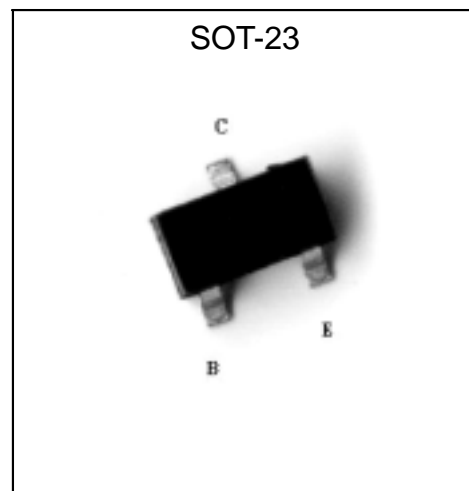
## Description

- The TFNA06 is designed for use in general purpose amplification and switching application.
- High current ,  $I_C = 0.5A$
- Low  $V_{CE(sat)}$  ,  $V_{CE(sat)} = 0.25V$ (typ.) at  $I_C/I_B = 100mA/10mA$
- Complementary to TFNA56.
- Pb-free package

## Symbol



## Outline



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CB0}$	80	V
Collector-Emitter Voltage	$V_{CE0}$	80	V
Emitter-Base Voltage	$V_{EB0}$	4	V
Collector Current	$I_C$	500	mA
Power Dissipation	$P_d$	225	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C



**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	80	-	-	V	I <sub>C</sub> =100μA
BV <sub>CEO</sub>	80	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	4	-	-	V	I <sub>E</sub> =100μA
I <sub>CB0</sub>	-	-	100	nA	V <sub>CB</sub> =80V
I <sub>CEO</sub>	-	-	100	nA	V <sub>CE</sub> =60V
*V <sub>CE(sat)</sub>	-	-	0.25	V	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA
*V <sub>BE(on)</sub>	-	-	1.2	V	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA
*h <sub>FE1</sub>	50	-	-	-	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA
*h <sub>FE2</sub>	50	-	-	-	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA
f <sub>T</sub>	100	-	-	MHz	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA, f=100MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

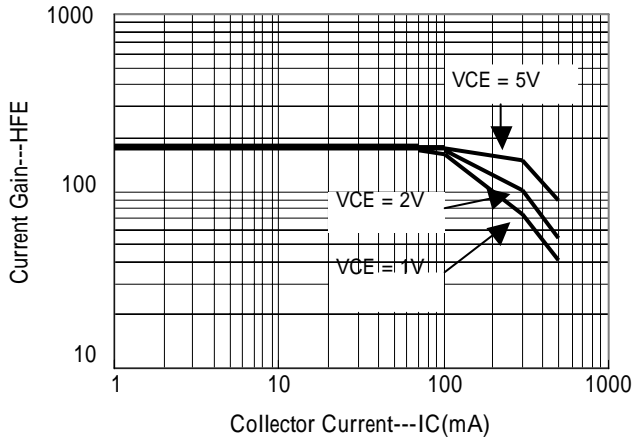
**Ordering Information**

Device	Package	Shipping	Marking
TFNA06	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	1G

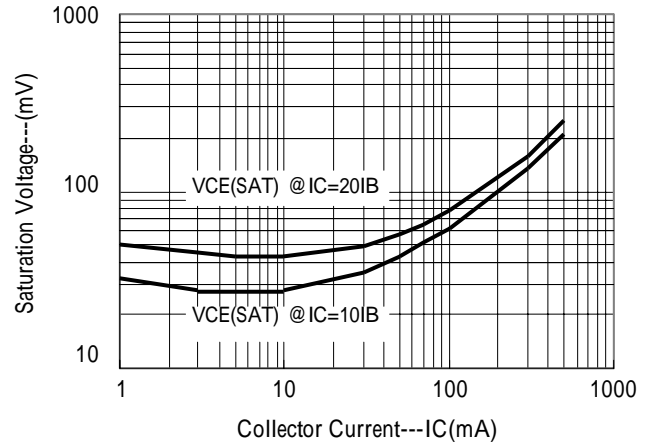


### Characteristic Curves

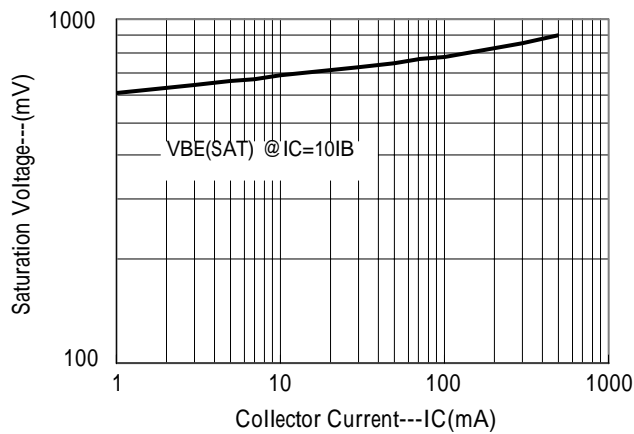
Current Gain vs Collector Current



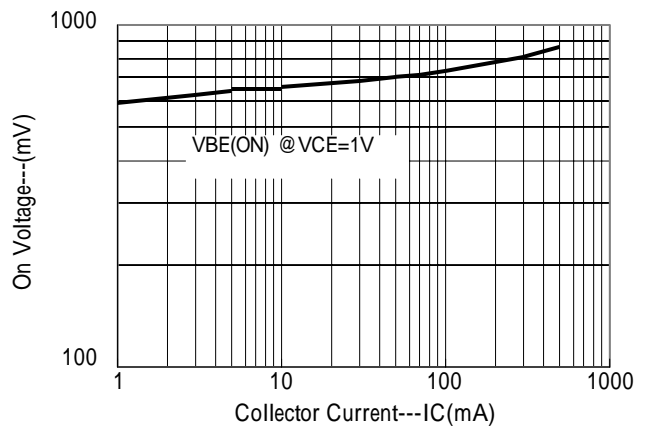
Saturation Voltage vs Collector Current



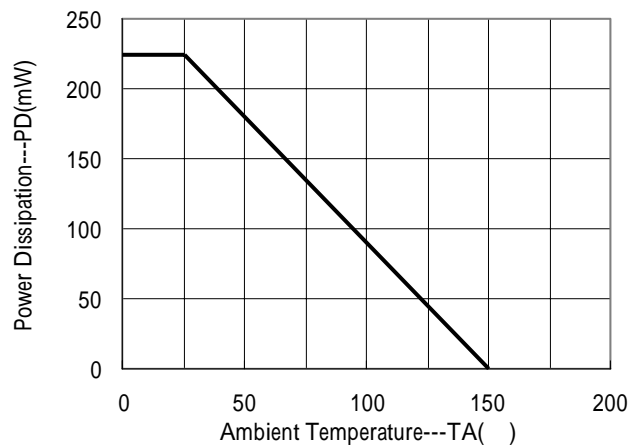
Saturation Voltage vs Collector Current



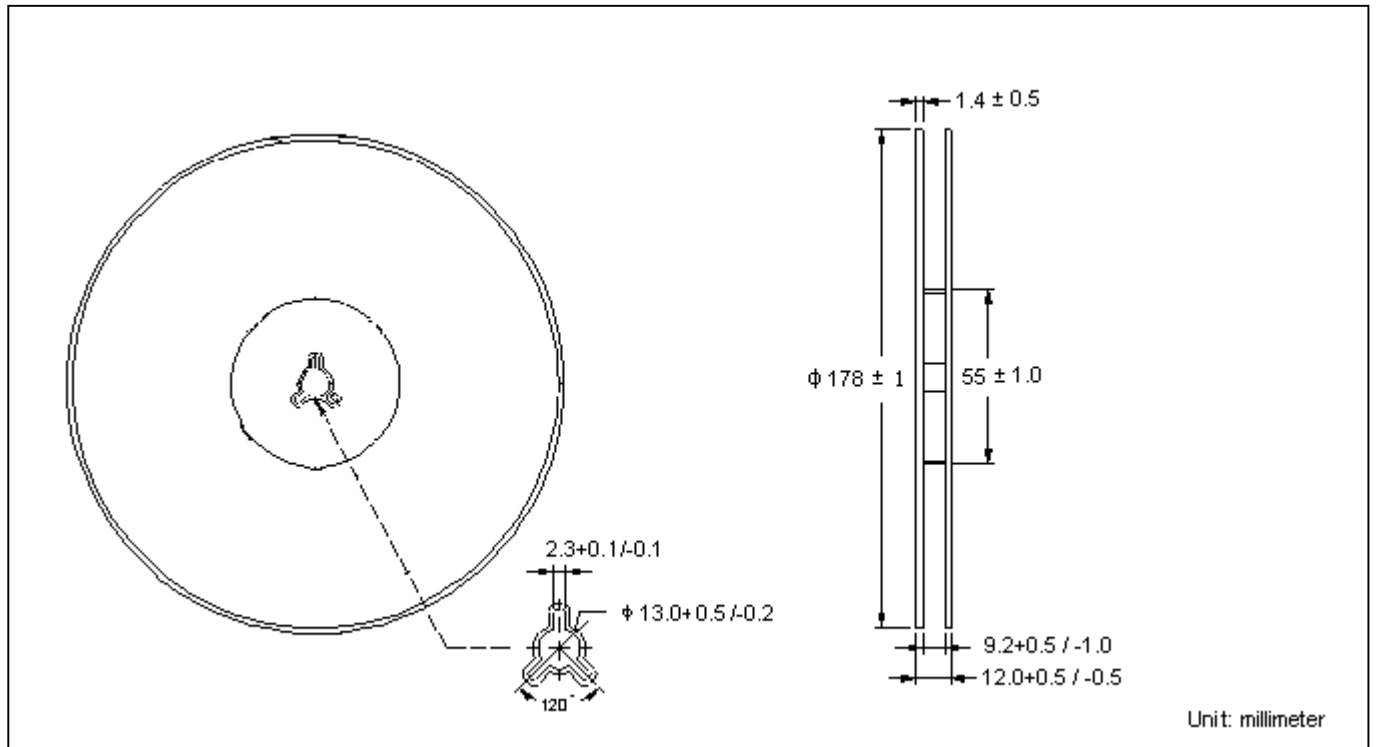
On Voltage vs Collector Current



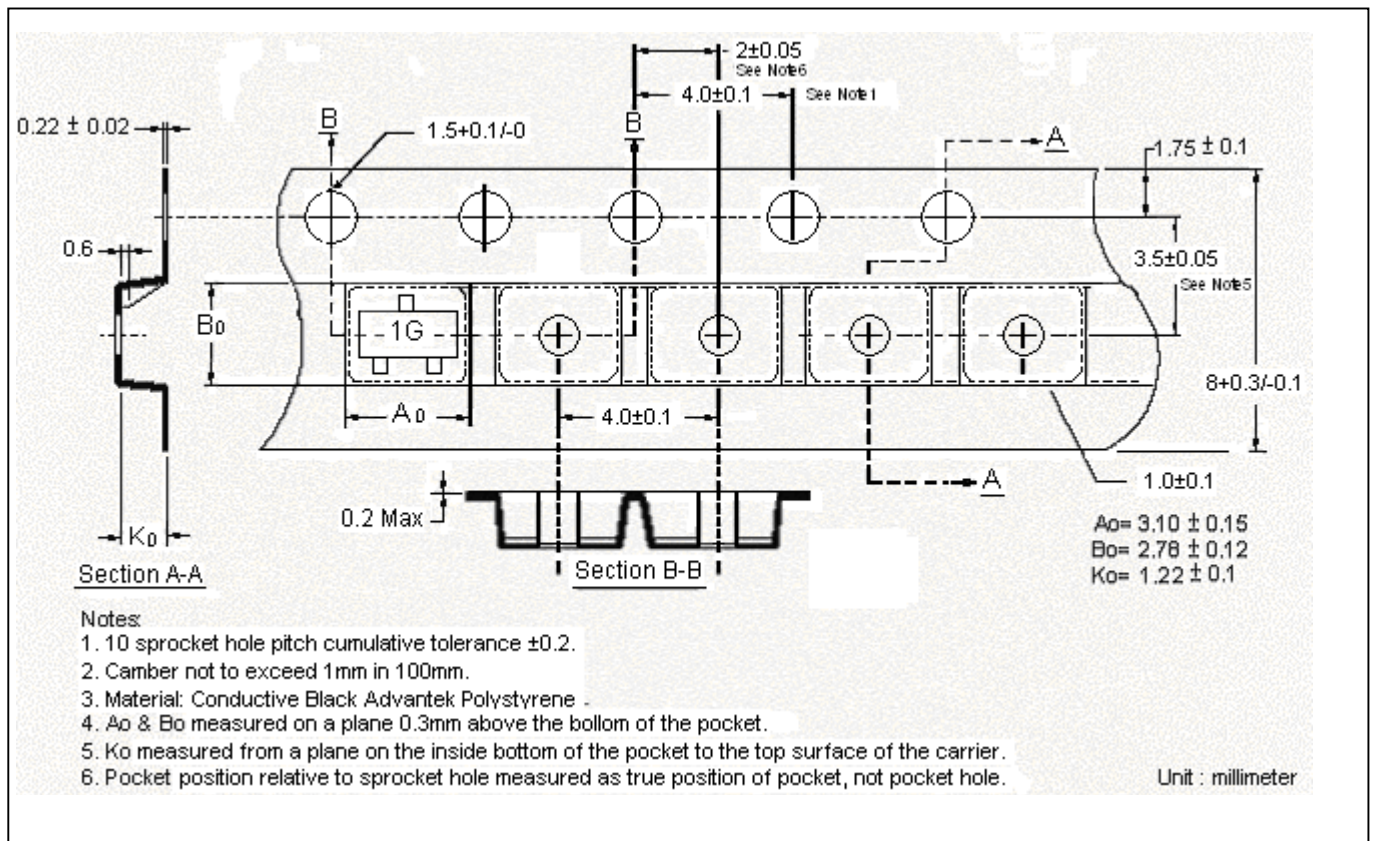
Power Derating Curve



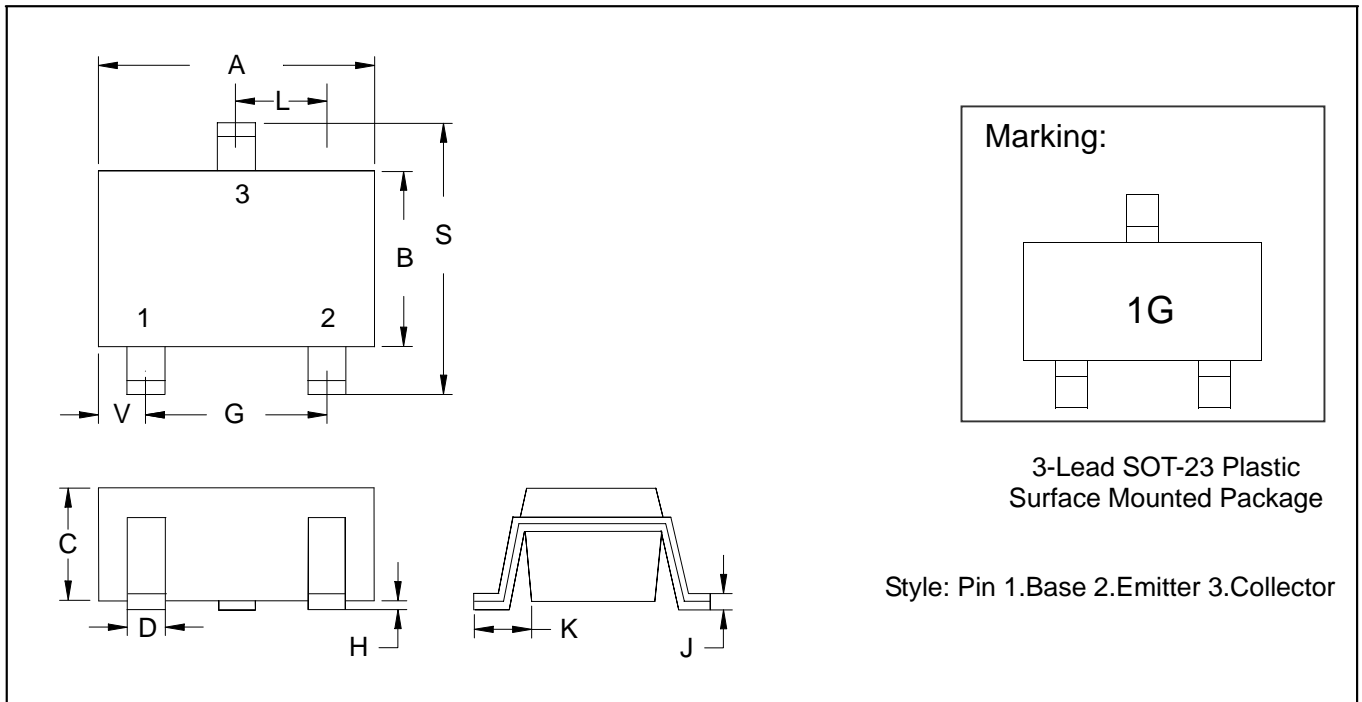
**Reel Dimension**



**Carrier Tape Dimension**



## SOT-23 Dimension



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local Tin Far sales office.

### Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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